onsemi

Complementary Power Transistors

DPAK for Surface Mount Applications

MJD44H11 (NPN), MJD45H11 (PNP)

Designed for general purpose power and switching such as output or driver stages in applications such as switching regulators, converters, and power amplifiers.

Features

- Lead Formed for Surface Mount Application in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("-1" Suffix)
- Electrically Similar to Popular D44H/D45H Series
- Low Collector Emitter Saturation Voltage
- Fast Switching Speeds
- Complementary Pairs Simplifies Designs
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

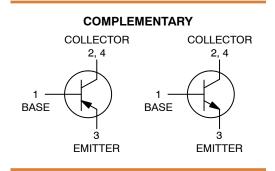
sign, -, ior FNF onnied, unless otherwise noted						
Rating	Symbol	Max	Unit			
Collector-Emitter Voltage	V _{CEO}	80	Vdc			
Emitter-Base Voltage	V _{EB}	5	Vdc			
Collector Current – Continuous	Ι _C	8	Adc			
Collector Current – Peak	I _{CM}	16	Adc			
Total Power Dissipation @ T _C = 25°C Derate above 25°C	PD	20 0.16	W W/°C			
Total Power Dissipation (Note 1) @ T _A = 25°C Derate above 25°C	P _D	1.75 0.014	W W/°C			
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C			
ESD – Human Body Model	HBM	3B	V			
ESD – Machine Model	MM	С	V			

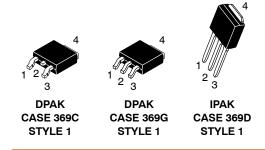
MAXIMUM RATINGS ($T_A = 25^{\circ}C$, common for NPN and PNP, minus sign, "–", for PNP omitted, unless otherwise noted)

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

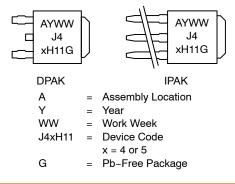
1. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

SILICON POWER TRANSISTORS 8 AMPERES 80 VOLTS, 20 WATTS





MARKING DIAGRAMS



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	6.25	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	71.4	°C/W
Lead Temperature for Soldering	ΤL	260	°C

2. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS

($T_A = 25^{\circ}C$, common for NPN and PNP, minus sign, "–", for PNP omitted, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					•
Collector-Emitter Sustaining Voltage $(I_{C} = 30 \text{ mA}, I_{B} = 0)$	V _{CEO(sus)}	80	-	-	Vdc
Collector Cutoff Current (V_{CE} = Rated V_{CEO} , V_{BE} = 0)	I _{CES}	_	_	1.0	μΑ
Emitter Cutoff Current (V _{EB} = 5 Vdc)	I _{EBO}	_	-	1.0	μΑ
ON CHARACTERISTICS					
Collector-Emitter Saturation Voltage $(I_{C} = 8 \text{ Adc}, I_{B} = 0.4 \text{ Adc})$	V _{CE(sat)}	_	-	1	Vdc
Base-Emitter Saturation Voltage (I _C = 8 Adc, I _B = 0.8 Adc)	V _{BE(sat)}	_	-	1.5	Vdc
DC Current Gain (V _{CE} = 1 Vdc, I _C = 2 Adc) (V _{CE} = 1 Vdc, I _C = 4 Adc)	h _{FE}	60 40			-
DYNAMIC CHARACTERISTICS					
Collector Capacitance (V _{CB} = 10 Vdc, f _{test} = 1 Mhz) MJD44H11 MJD45H11	C _{cb}	- -	45 130		pF
Gain Bandwidth Product (I _C = 0.5 Adc, V _{CE} = 10 Vdc, f = 20 Mhz) MJD44H11 MJD45H11	fT	-	85 90	-	MHz
SWITCHING TIMES			-		•
Delay and Rise Times (I _C = 5 Adc, I _{B1} = 0.5 Adc) MJD44H11 MJD45H11	t _d + t _r	-	300 135	-	ns
Storage Time (I _C = 5 Adc, I _{B1} = I _{B2} = 0.5 Adc) MJD44H11 MJD45H11	ts		500 500	-	ns
Fall Time (I _C = 5 Adc, I _{B1} = I _{B2} = 0.5 Adc) MJD44H11 MJD45H11	t _f	-	140 100	-	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

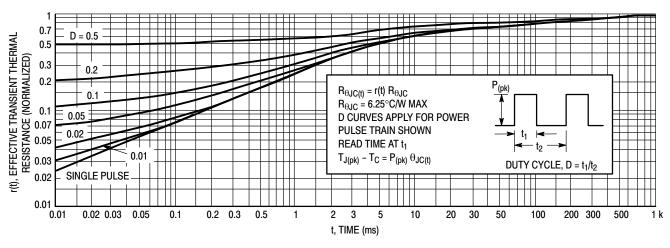
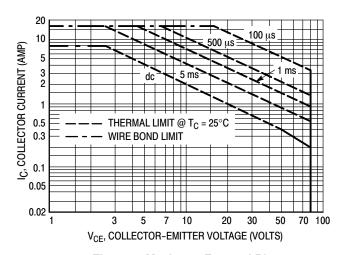
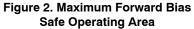


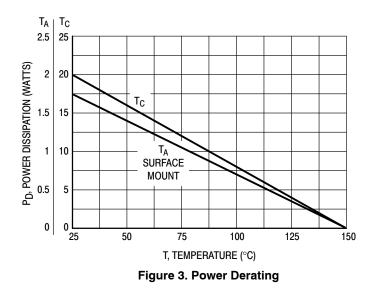
Figure 1. Thermal Response

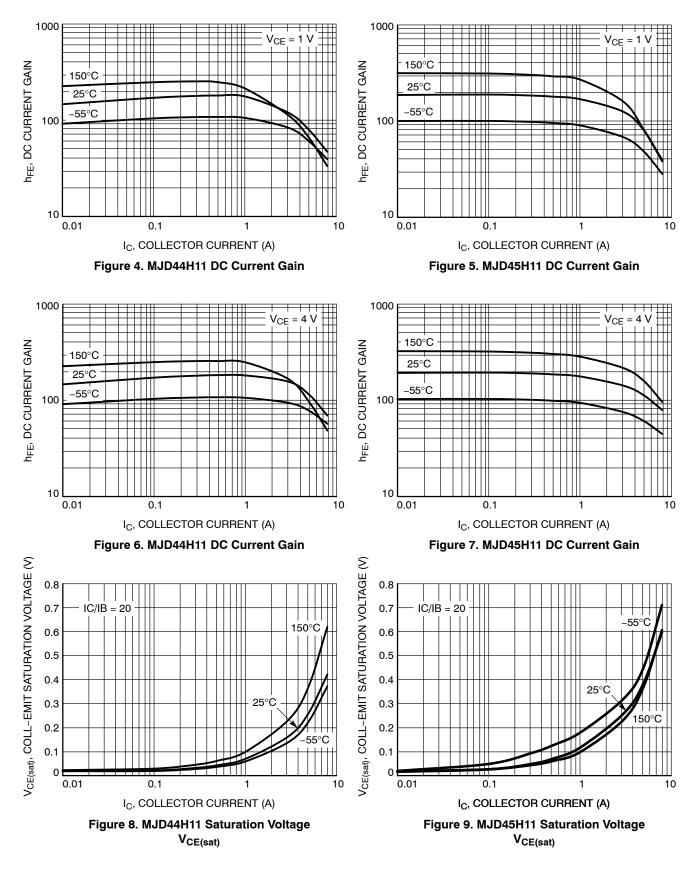


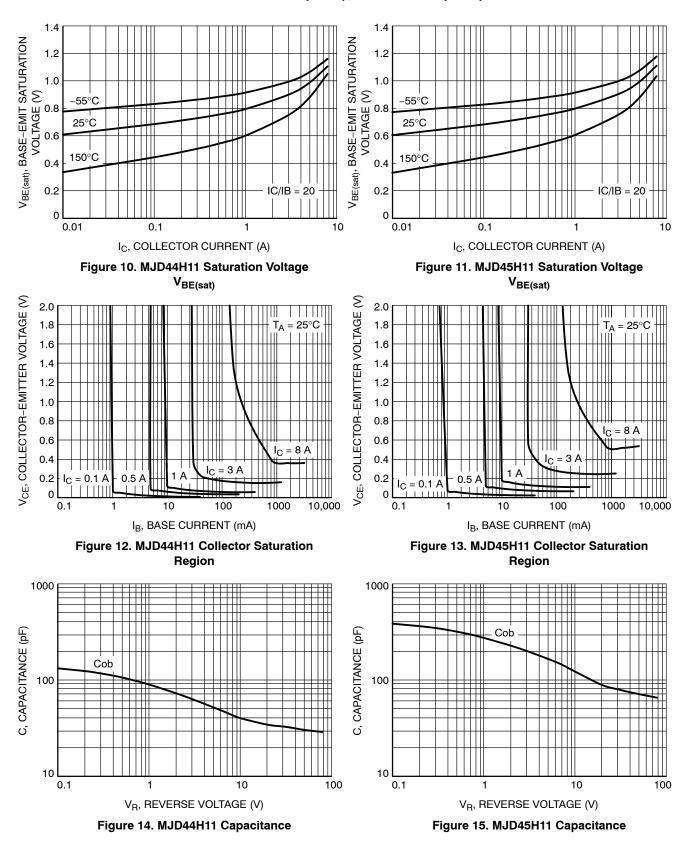


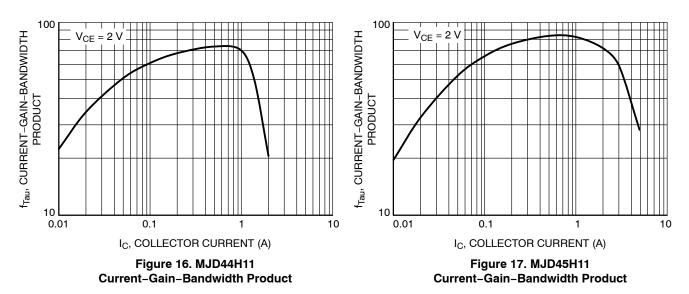
There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on $T_{J(pk)} = 150^{\circ}$ C; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}$ C. $T_{J(pk)}$ may be calculated from the data in Figure 1. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.









ORDERING INFORMATION

Device	Package Type	Package	Shipping [†]
MJD44H11G	DPAK (Pb-Free)	369C	75 Units / Rail
NJVMJD44H11G	DPAK (Pb-Free)	369C	75 Units / Rail
MJD44H11-1G	DPAK-3 (Pb-Free)	369D	75 Units / Rail
MJD44H11RLG	DPAK (Pb-Free)	369C	1,800 / Tape & Reel
NJVMJD44H11RLG*	DPAK (Pb-Free)	369C	1,800 / Tape & Reel
MJD44H11T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD44H11T4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
MJD44H11T5G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
MJD45H11G	DPAK (Pb-Free)	369C	75 Units / Rail
NJVMJD45H11G*	DPAK (Pb-Free)	369C	75 Units / Rail
MJD45H11-1G	DPAK-3 (Pb-Free)	369D	75 Units / Rail
MJD45H11RLG	DPAK (Pb-Free)	369C	1,800 / Tape & Reel
NJVMJD45H11RLG*	DPAK (Pb-Free)	369C	1,800 / Tape & Reel
MJD45H11T4G	DPAK (Pb–Free)	369C	2,500 / Tape & Reel
NJVMJD45H11T4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD44H11D3T4G*	DPAK (Pb–Free)	369G	2,500 / Tape & Reel
NJVMJD45H11D3T4G*	DPAK (Pb-Free)	369G	2,500 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP

Capable



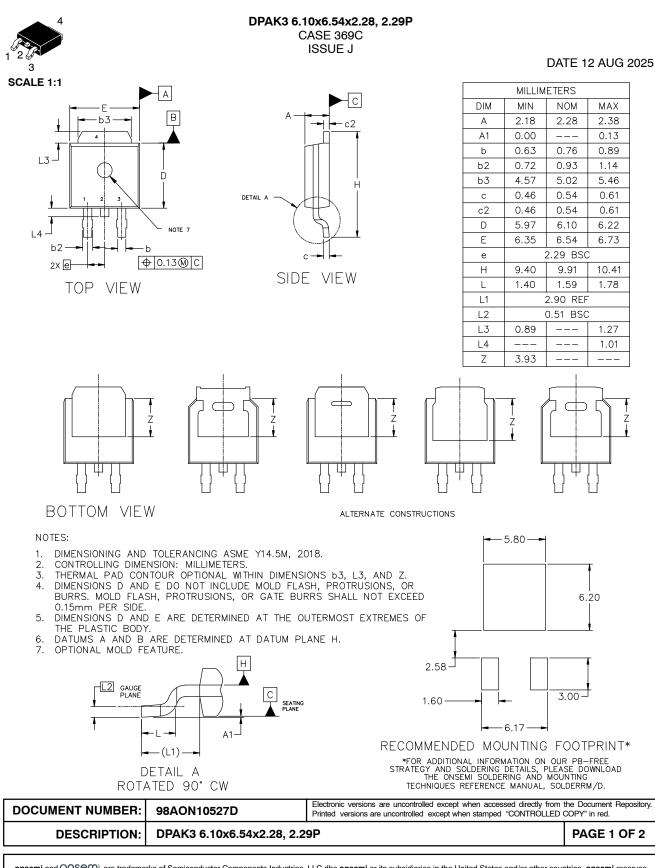
DPAK INSERTION MOUNT CASE 369 ISSUE O DATE 02 JAN 2000 SCALE 1:1 С $B \rightarrow$ NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. Е R MILLIMETERS INCHES л DIM MIN MAX MIN MAX A 0.235 0.250 B 0.250 0.265 5.97 6.35 Δ 6.35 6.73 C 0.086 0.094 D 0.027 0.035 2.19 0.69 2.38 2 3 0.88 S E 0.033 0.040 F 0.037 0.047 0.84 1.01 0.94 -T-1.19 G 0.090 BSC 2.29 BSC SEATING H 0.034 0.040 J 0.018 0.023 0.87 1.01 0.46 0.58 K 0.350 0.380 8.89 9.65 **R** 0.175 0.215 4.45 5.46 0.050 0.090 1.27 J S 2.28 F V 0.030 0.050 н 0.77 1.27 D 3 PL G 🔫 ⊕ 0.13 (0.005) M T

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:		STYLE 5:		STYLE 6:	
PIN 1.	BASE	PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	CATHODE	PIN 1.	GATE	PIN 1.	MT1
2.	COLLECTOR	2.	DRAIN	2.	CATHODE	2.	ANODE	2.	ANODE	2.	MT2
3.	EMITTER	3.	SOURCE	3.	ANODE	3.	GATE	3.	CATHODE	3.	GATE
4.	COLLECTOR	4.	DRAIN	4.	CATHODE	4.	ANODE	4.	ANODE	4.	MT2

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DESCRIPTION: DPAK INSERTION MOUNT PAGE 1 OF	DESCRIPTION:	RIPTION: DPAK INSERTION MOUNT		PAGE 1 OF 1

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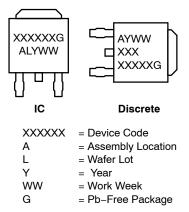


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DPAK3 6.10x6.54x2.28, 2.29P CASE 369C ISSUE J

DATE 12 AUG 2025

GENERIC MARKING DIAGRAM*



*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. BASE 2. COLLE 3. EMITT 4. COLLE	ER 3. SOL	IN 2. CA JRCE 3. AN	STYLE 4: NODE PIN 1. CA NTHODE 2. AN NODE 3. GA NTHODE 4. AN	IODE 2. ANODE TE 3. CATHODE
STYLE 6: PIN 1. MT1 2. MT2 3. GATE 4. MT2	STYLE 7: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	3. ANODE	3. RESISTOR	ADJUST 3. CATHODE

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DESCRIPTION:	DPAK3 6.10x6.54x2.28, 2.29P		PAGE 2 OF 2

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NSEM

		CAS	JRFACE MOUNT SE 369G SUE O	
SCALE 1:1				
$V \xrightarrow{4}$	A A ↓ K M J – H – D 2 PL ⊕ 0.13 (0.005)	C - E C U U T		Ni 1 2
STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE	STYLE 4: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE	
STYLE 5: PIN 1. GATE 2. ANODE 3. CATHODE 4. ANODE	STYLE 6: PIN 1. MT1 2. MT2 3. GATE 4. MT2	STYLE 7: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR		xxx Y W\

DATE 23 DEC 2003

NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INC	HES	MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.22
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
Е	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.180 BSC 4.58		BSC	
н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
κ	0.102	0.114	2.60	2.89
L	0.090	BSC	2.29 BSC	
R	0.180	0.215	4.57	5.45
U	0.020		0.51	
V	0.035	0.050	0.89	1.27
Z	0.155		3.93	

GENERIC **MARKING DIAGRAM***



xxxxxxxx = Device Code = Year ww = Work Week

*This information is generic. Please refer to device data sheet for actual part marking.

DOCUMENT NUMBER:	98AON13702D Electronic versions are uncontrolled except when accessed directly from the Docu Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in			
DESCRIPTION:	DPAK-3, SURFACE MOUNT		PAGE 1 OF 1	

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